

## isc Silicon NPN Power Transistor

## **BU508A**

#### DESCRIPTION

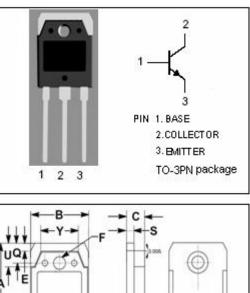
- Collector-Emitter Sustaining Voltage-
- : V<sub>CEO(SUS)</sub>= 700V (Min)
- High Power Dissipation-
  - : P₀= 125W@T₀= 25℃
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

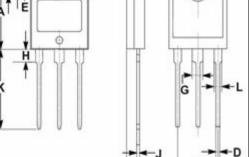
#### **APPLICATIONS**

• Designed for use in large screen color deflection circuits.

ADSULU	ABSOLUTE MAXIMUM RATINGS(Ta=25 C)								
SYMBOL	PARAMETER	v	ALUE	UNIT					
V <sub>CES</sub>	Collector- Emitter Voltage(V <sub>BE</sub> = 0)	1500		v					
V <sub>CEO</sub>	Collector-Emitter Voltage	700		v					
V <sub>EBO</sub>	Emitter-Base Voltage	5		V					
lc	Collector Current- Continuous	8		А					
I <sub>CM</sub>	Collector Current-Peak	15		А					
lв	Base Current- Continuous	4		А					
I <sub>BM</sub>	Base Current-Peak	6		А					
Pc	Collector Power Dissipation @ $T_c$ =25 °C	125		W					
TJ	Junction Temperature	150		°C					
T <sub>stg</sub>	Storage Temperature Range	-65~150		°C					
SYMBOL	PARAMETER		МАХ	UNIT					

#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





R

	mm	
DIM	MIN	MAX
Α	19.60	20.10
В	15.50	15.70
С	4.70	4.90
D	0.90	1.10
Ε	1.90	2.10
F	3.40	3.60
G	2.90	3.20
Н	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

isc website: www.iscsemi.com

Rth j-c

Thermal Resistance, Junction to Case

1.0

°C/W

<sup>1</sup> *isc & iscsemi* is registered trademark



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### ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA ; I <sub>B</sub> = 0	700			V
Vce(sat)★	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 2.0A			1.0	V
V <sub>BE(sat)</sub> ★	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 2.0A			1.3	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1500V ; V <sub>BE</sub> = 0 V <sub>CE</sub> = 1500V ; V <sub>BE</sub> = 0; T <sub>C</sub> =125℃			1.0 2.0	mA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 5.0V ; I <sub>C</sub> = 0			0.1	mA
hfe	DC Current Gain	I <sub>C</sub> = 0.1A ; V <sub>CE</sub> = 5V	6		30	
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 0.1MHz		125		pF
fT	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V; f <sub>test</sub> = 1.0MHz		7		MHz

★:Pulsed: Pulse duration = 300 ms, duty cycle 1.5 %

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